Product data sheet

1. Product profile

1.1 General description

Single high-speed switching diode, encapsulated in a SOD323F (SC-90) very small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- High switching speed: $t_{rr} \le 4$ ns
- Low leakage current
- Repetitive peak reverse voltage: V_{RRM} ≤ 100 V
- Excellent coplanarity and improved thermal behavior
- Low capacitance: C_d ≤ 1.5 pF
- Reverse voltage: V_R ≤ 100 V
- Very small and flat lead SMD plastic package

1.3 Applications

- High-speed switching
- General-purpose switching
- Voltage clamping
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		<u>[1]</u> _	-	250	mA
I _R	reverse current	$V_R = 75 V$	-	-	1	μΑ
V_R	reverse voltage		-	-	100	V
t _{rr}	reverse recovery time		[2] _	-	4	ns

^[1] Pulse test: $t_0 \le 300 \,\mu\text{s}$; $\delta \le 0.02$.



^[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

Single high-speed switching diode

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	1.4
2	anode	1 2	+
			sym006

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BAS16J	SC-90	plastic surface-mounted package; 2 leads	SOD323F

4. Marking

Table 4. Marking codes

Type number	Marking code
BAS16J	AR

Single high-speed switching diode

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 , (,		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	100	V
V_R	reverse voltage		-	100	V
I _F	forward current		<u>[1]</u> -	250	mA
I _{FRM}	repetitive peak forward current	$t_p \leq 0.5 \text{ ms}; \\ \delta \leq 0.25$	-	500	mA
I _{FSM}	non-repetitive peak forward current	square wave	[2]		
		$t_p = 100 \; \mu s$	-	3.3	Α
		$t_p = 1 \text{ ms}$	-	2	Α
		$t_p = 10 \text{ ms}$	-	1.5	А
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3][4]	550	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	230	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[3] -	-	55	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] $T_i = 25$ °C prior to surge.

^[3] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm²

^[4] Reflow soldering is the only recommended soldering method.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Soldering point of cathode tab.

Single high-speed switching diode

7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

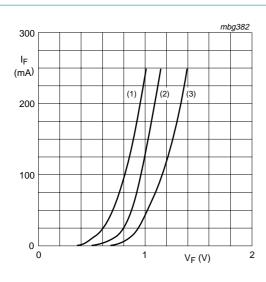
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>				
		I _F = 1 mA		-	-	715	mV
		I _F = 10 mA		-	-	855	mV
		I _F = 50 mA		-	-	1	V
		I _F = 150 mA		-	-	1.25	V
I _R reverse current	reverse current	V _R = 25 V		-	-	30	nA
	V _R = 75 V		-	-	1	μΑ	
	V _R = 25 V; T _j = 150 °C		-	-	30	μΑ	
		V _R = 75 V; T _j = 150 °C		-	-	50	μΑ
C _d	diode capacitance	$V_R = 0 V$; $f = 1 MHz$		-	-	1.5	pF
t _{rr}	reverse recovery time		[2]	-	-	4	ns
V_{FR}	forward recovery voltage		[3]	-	-	1.75	V

^[1] Pulse test: $t_0 \le 300 \,\mu\text{s}$; $\delta \le 0.02$.

^[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

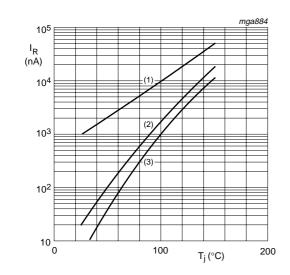
^[3] When switched from $I_F = 10$ mA; $t_r = 20$ ns.

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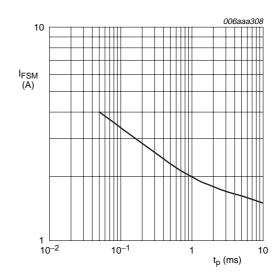
- (1) $T_{amb} = 150 \,^{\circ}C$; typical values
- (2) $T_{amb} = 25 \,^{\circ}C$; typical values
- (3) $T_{amb} = 25 \,^{\circ}C$; maximum values

Fig 1. Forward current as a function of forward voltage



- (1) $V_R = 75 \text{ V}$; maximum values
- (2) $V_R = 75 V$; typical values
- (3) $V_R = 25 V$; typical values

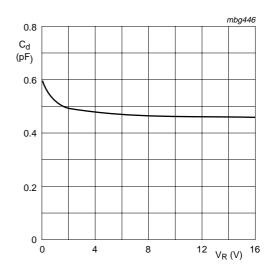
Fig 3. Reverse current as a function of junction temperature



Based on square wave currents.

 $T_j = 25$ °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



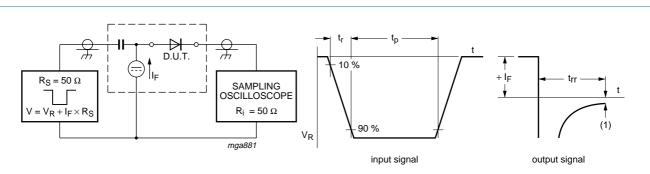
 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

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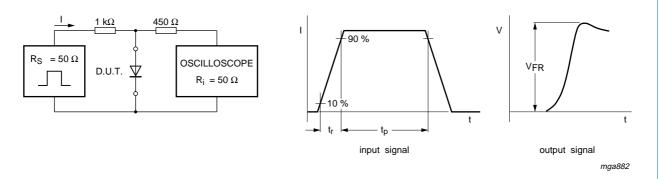
Single high-speed switching diode

8. Test information



(1) $I_R = 1$ mA Input signal: reverse pulse rise time $t_r = 0.6$ ns; reverse voltage pulse duration $t_p = 100$ ns; duty cycle $\delta = 0.05$ Oscilloscope: rise time $t_r = 0.35$ ns

Fig 5. Reverse recovery time test circuit and waveforms

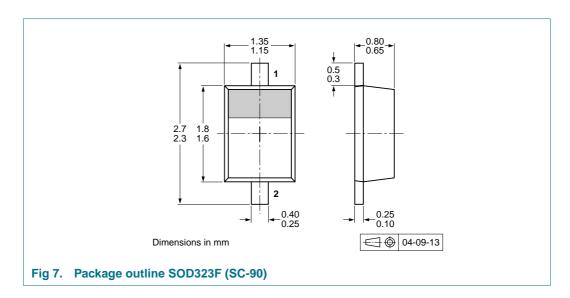


Input signal: forward pulse rise time t_r = 20 ns; forward current pulse duration $t_p \ge 100$ ns; duty cycle $\delta \le 0.005$

Fig 6. Forward recovery voltage test circuit and waveforms

Single high-speed switching diode

9. Package outline



10. Packing information

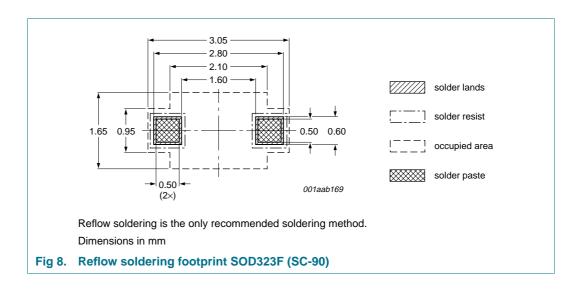
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	antity
			3000	10000
BAS16J	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



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Single high-speed switching diode

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAS16J_1	20070308	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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